

TO-220 Plastic-Encapsulate Diodes

HYPERFAST RECTIFIER,FRED

MAIN CHARACTERISTICS

I_O	30A
V_{RRM}	600V
T_{rr}	21ns
T_j	175°C
$V_{F(typ)}$	1.55V(@ $T_j=150^\circ\text{C}$)

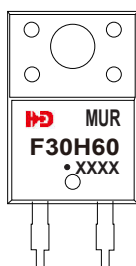
FEATURES

- Ultrafast Recovery Times and Low Recovery Loss
- Low Forward Voltage
- Low Reverse Leakage Current

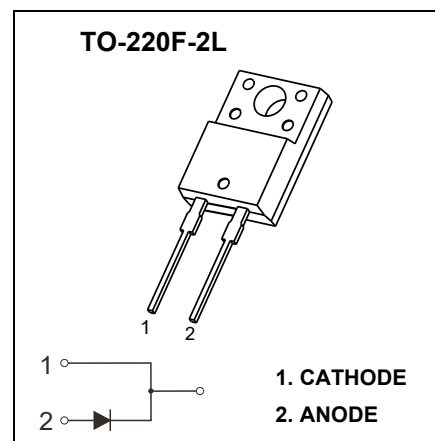
APPLICATIONS

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MARKING



MURF30H60 = Device code
Solid dot = Green molding compound device
if none, the normal device
XXXX = Code



MAXIMUM RATINGS ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	MURF30H60	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	600	V
V_R	DC Blocking Voltage		
$I_{F(AV)}$	Average Forward Current($T_c=54^\circ\text{C}$)	30	A
$I_{F(RMS)}$	RMS Forward Current($T_c=54^\circ\text{C}$)	42	A
I_{FSM}	Non-Repetitive Surge Forward Current (8.3ms)	250	A
P_D	Power dissipation	58	W
$R_{\theta JC}$	Thermal Resistance From Junction to Case	2.6	$^\circ\text{C}/\text{W}$
T_j	Operating Junction Temperature Range	-55 ~ +175	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55 ~ +175	$^\circ\text{C}$

Typical Characteristics

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified)

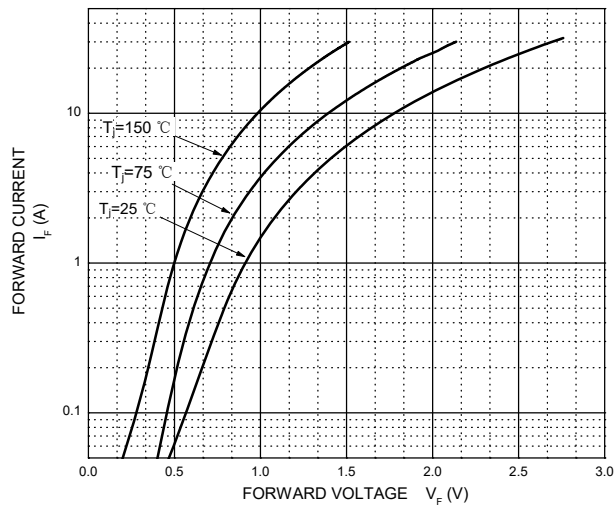
Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$V_{(BR)}$	Reverse Voltage	IR=100 μ A		600			V
I_R	Reverse Current	VR=600V	$T_j=25^\circ\text{C}$			10	μ A
			$T_j=150^\circ\text{C}$			1	mA
V_F	Forward Voltage	IF=30A	$T_j=25^\circ\text{C}$		2.7	3	V
			$T_j=150^\circ\text{C}$		1.55		V
C_{tot}	Total Capacitance	VR=200V, f=1MHz			100		pF
trr	Reverse Recovery time	IF=0.5A, IR=1A, Irr=0.25A			32		ns
		IF=1A, VR=30V, $di_f/dt = 200\text{A}/\mu\text{s}$			21		ns

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified)

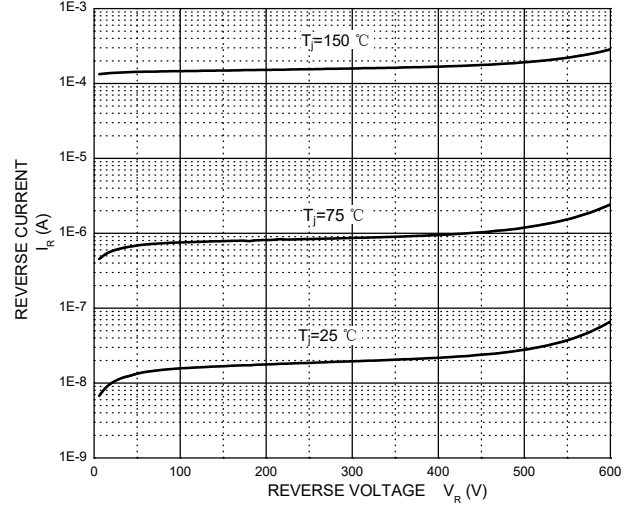
Symbol	Parameter	Test Comditions	Min.	Typ.	Max.	Unit
trr	Reverse Recovery Time	IF=30A, VR=400V, $di_f/dt=200\text{A}/\mu\text{s}$		29		ns
I_{RRM}	Max. Reverse Recovery Current			1.9		A
Qrr	Reverse Recovery Charge			32		nC
trr	Reverse Recovery Time	IF=30A, VR=400V, $di_f/dt=200\text{A}/\mu\text{s}$, $T_j=125^\circ\text{C}$		60		ns
I_{RRM}	Max. Reverse Recovery Current			6		A
Qrr	Reverse Recovery Charge			201		nC
trr	Reverse Recovery Time	IF=30A, VR=400V, $di_f/dt=600\text{A}/\mu\text{s}$, $T_j=125^\circ\text{C}$		39		ns
I_{RRM}	Max. Reverse Recovery Current			14		A
Qrr	Reverse Recovery Charge			359		nC

Typical Characteristics

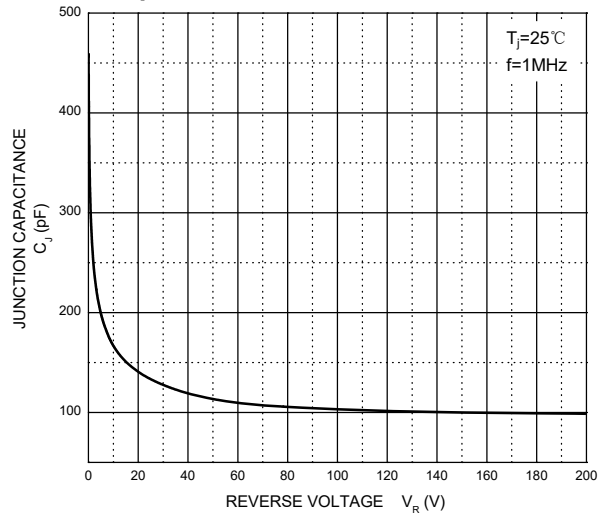
Forward Characteristics



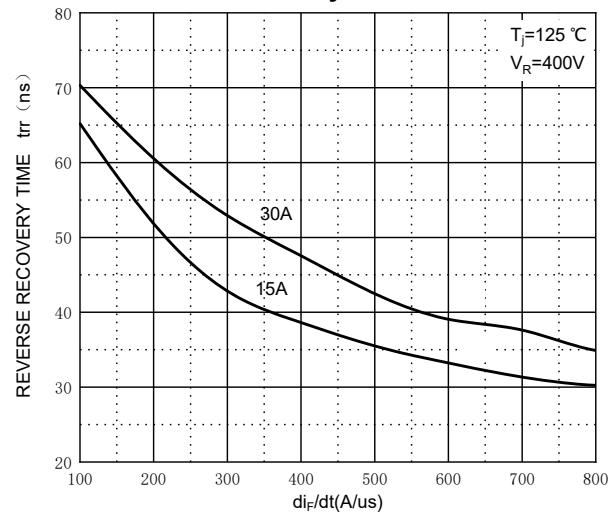
Reverse Characteristics



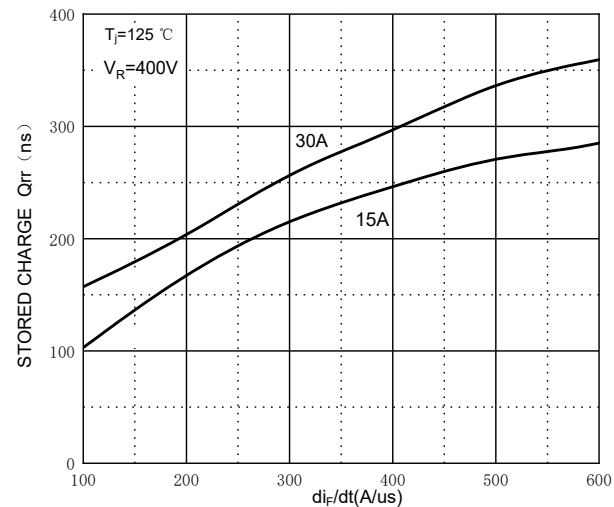
Capacitance Characteristics Per Diode



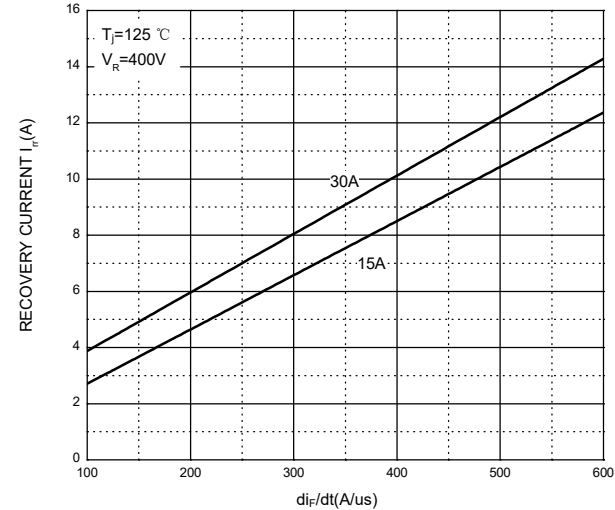
Reverse Recovery Time vs. di_F/dt



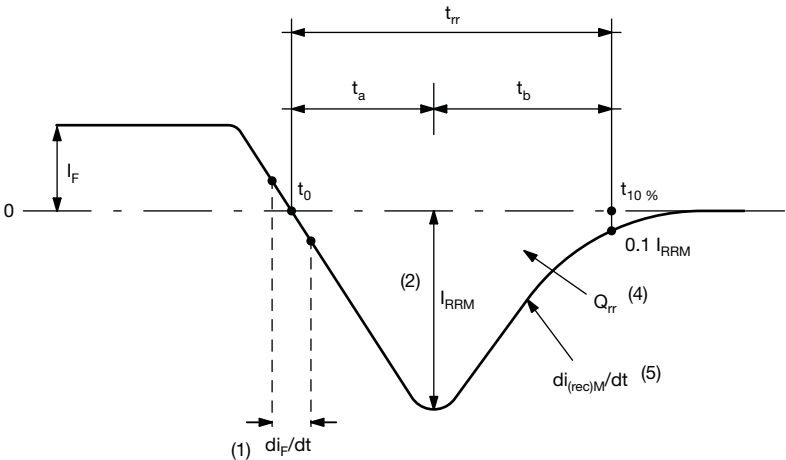
Stored Charge vs. di_F/dt



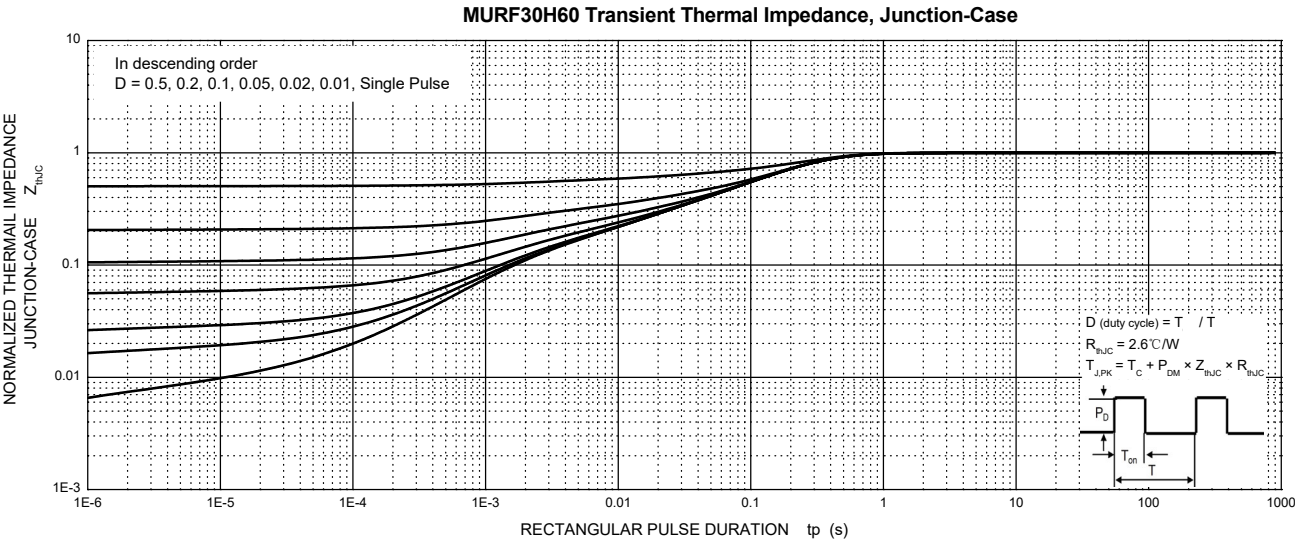
Recovery Current vs. di_F/dt



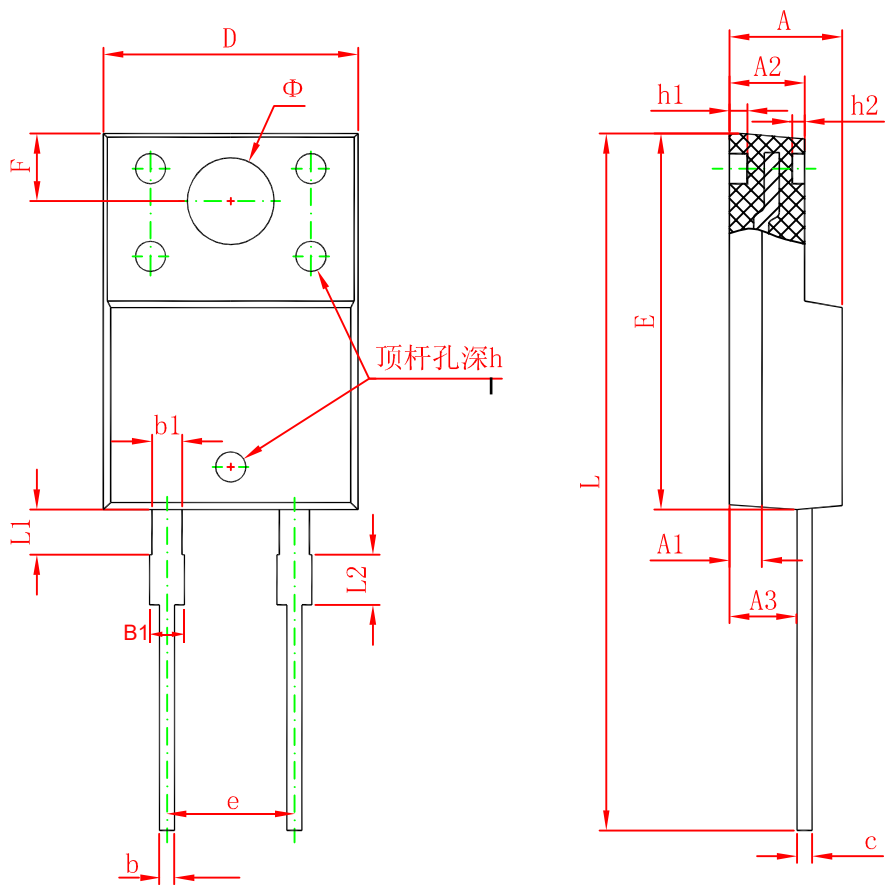
Typical Characteristics



Reverse Recovery Waveform and Definitions



TO-220F-2L Package Outline Dimensions



Symbol			Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.300	4.700	0.169	0.185
A1	1.200 REF.		0.047 REF.	
A2	2.800	3.200	0.110	0.126
A3	2.500	2.900	0.098	0.114
b	0.710	0.910	0.028	0.036
b1	1.100	1.350	0.043	0.053
B1	1.150	1.400	0.045	0.055
c	0.500	0.750	0.020	0.030
D	9.960	10.360	0.392	0.408
E	14.800	15.200	0.583	0.598
e	5.080 TYP.		0.200 TYP.	
F	2.700 REF.		0.106 REF.	
Φ	3.300 REF.		0.130 REF.	
h	0.000	0.300	0.000	0.012
h1	0.800 REF.		0.031 REF.	
h2	0.500 REF.		0.020 REF.	
L	28.000	28.400	1.102	1.118
L1	2.100	2.400	0.082	0.094
L2	1.300	1.700	0.051	0.066